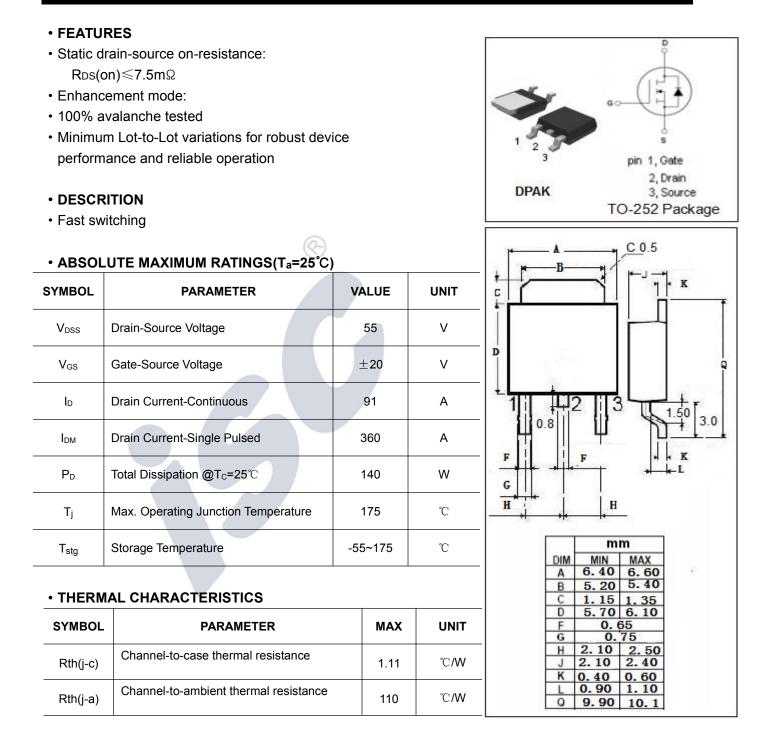


### **INCHANGE SEMICONDUCTOR**

## isc N-Channel MOSFET Transistor

# IRFR1010Z, IIRFR1010Z





## isc N-Channel MOSFET Transistor IRFR1010Z, IIRFR1010Z

### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	55			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	VDS=VGS; I <sub>D</sub> =100 µ A	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =42A			7.5	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.2	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =55V; V <sub>GS</sub> = 0V			20	μA
V <sub>SD</sub>	Diode forward voltage	I <sub>s</sub> =42A, V <sub>GS</sub> = 0V			1.3	V

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